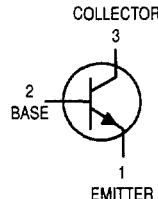


Switching Transistors

NPN Silicon

MPS2369
MPS2369A*

*Motorola Preferred Device



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	15	Vdc
Collector-Emitter Voltage	VCES	40	Vdc
Collector-Base Voltage	VCBO	40	Vdc
Emitter-Base Voltage	VEBO	4.5	Vdc
Collector Current — Continuous	I _C	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R _{θJA}	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ⁽¹⁾ (I _C = 10 mAdc, I _B = 0)	V(BR)CEO	15	—	—	Vdc
Collector-Emitter Breakdown Voltage (I _C = 10 μAdc, V _{BE} = 0)	V(BR)CES	40	—	—	Vdc
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V(BR)CBO	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V(BR)EBO	4.5	—	—	Vdc
Collector Cutoff Current (V _{CB} = 20 Vdc, I _E = 0) (V _{CB} = 20 Vdc, I _E = 0, T _A = 125°C)	I _{CBO}	— —	— —	0.4 30	μAdc
Collector Cutoff Current (V _{CE} = 20 Vdc, V _{BE} = 0)	I _{CES}	—	—	0.4	μAdc

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

MPS2369 MPS2369A
ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ⁽¹⁾ (IC = 10 mAdc, VCE = 1.0 Vdc) (IC = 10 mAdc, VCE = 1.0 Vdc, TA = -55°C) (IC = 10 mAdc, VCE = 1.0 Vdc) (IC = 10 mAdc, VCE = 0.35 Vdc) (IC = 10 mAdc, VCE = 0.35 Vdc, TA = -55°C) (IC = 30 mAdc, VCE = 0.4 Vdc) (IC = 100 mAdc, VCE = 2.0 Vdc) (IC = 100 mAdc, VCE = 1.0 Vdc)	hFE MPS2369A MPS2369 MPS2369 MPS2369A MPS2369A MPS2369A MPS2369	— 20 40 40 20 30 20 20	— — — — — — — —	120 — 120 — — — — —	—
Collector-Emitter Saturation Voltage ⁽¹⁾ (IC = 10 mAdc, IB = 1.0 mAdc) (IC = 10 mAdc, IB = 1.0 mAdc) (IC = 10 mAdc, IB = 1.0 mAdc, TA = +125°C) (IC = 30 mAdc, IB = 3.0 mAdc) (IC = 100 mAdc, IB = 10 mAdc)	VCE(sat) MPS2369 MPS2369A MPS2369A MPS2369A MPS2369A	— — — — —	— — — — —	0.25 0.20 0.30 0.25 0.50	Vdc
Base-Emitter Saturation Voltage ⁽¹⁾ (IC = 10 mAdc, IB = 1.0 mAdc) (IC = 10 mAdc, IB = 1.0 mAdc, TA = +125°C) (IC = 10 mAdc, IB = 1.0 mAdc, TA = -55°C) (IC = 30 mAdc, IB = 3.0 mAdc) (IC = 100 mAdc, IB = 10 mAdc)	VBE(sat) MPS2369 MPS2369A MPS2369A MPS2369A MPS2369A	0.7 0.5 — — —	— — — — —	0.85 — 1.02 1.15 1.60	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo} MPS2369,A	—	—	4.0	pF
Small-Signal Current Gain (IC = 10 mAdc, VCE = 10 Vdc, f = 100 MHz)	h _{fe} MPS2369,A	5.0	—	—	—
SWITCHING CHARACTERISTICS					
Storage Time (IB1 = IB2 = IC = 10 mAdc) (Figure 3)	t _S MPS2369,A	—	5.0	13	ns
Turn-On Time (V _{CC} = 3.0 Vdc, IC = 10 mAdc, IB1 = 3.0 mAdc, (Figure 1))	t _{on} MPS2369,A	—	8.0	12	ns
Turn-Off Time (V _{CC} = 3.0 Vdc, IC = 10 mAdc, IB1 = 3.0 mAdc, IB2 = 1.5 mAdc) (Figure 2)	t _{off} MPS2369,A	—	10	18	ns

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

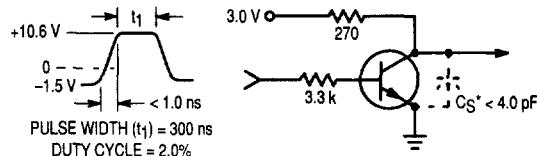
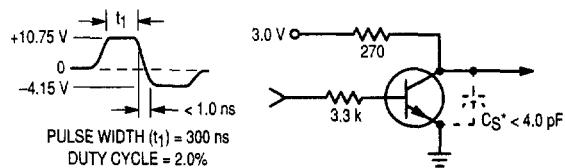
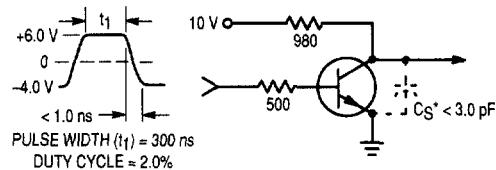
Figure 1. t_{on} CircuitFigure 2. t_{off} Circuit

Figure 3. Storage Test Circuit

* Total shunt capacitance of test jig and connectors.